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Yan-Ny Tan; Chim, W.-K.; Byung Jin Cho; Wee-Kiong Choi; Electron Devices, IEEE Transactions on Volume 51, Issue 7, July 2004 Page(s):1143 - 1147

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2. Preliminary investigation of hafnium oxide deposited via atomic layer chemical v (ALCVD)

Conley, J.F., Jr.; Ono, Y.; Tweet, D.J.; Zhuang, W.; Khaiser, M.; Solanki, R.; Integrated Reliability Workshop Final Report, 2001. 2001 IEEE International 15-18 Oct. 2001 Page(s):11 - 15

[AbstractPlus](#) | [Full Text: PDF\(516 KB\)](#) IEEE CNF


3. Ultrathin hafnium oxide with low leakage and excellent reliability for alternative g application

Byoung Hun Lee; Laegu Kang; Wen-Jie Qi; Renee Nieh; Yongjoo Jeon; Katsunori Ono; Electron Devices Meeting, 1999. IEDM Technical Digest. International 5-8 Dec. 1999 Page(s):133 - 136

[AbstractPlus](#) | [Full Text: PDF\(324 KB\)](#) IEEE CNF


4. Reliability physics and chemistry of thin and high-k gate oxides

Lenahan, P.; Integrated Reliability Workshop Final Report, 2003 IEEE International 20-23 Oct. 2003 Page(s):175

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L3	8	dielectric adj constant and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:23
L4	296	applied adj materials and high adj dielectric adj constant and table	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 12:24
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